

2.5V Operation Fundamental Frequency Crystal Oscillator Module ICs

OVERVIEW

The CF5015 series are 2.5V operation crystal oscillator ICs. They are available for frequencies up to 60MHz. The product lineup consists of AL× series for 2.5V exclusive use and BL× series compliant with 2.5V to 5V. The built-in oscillator capacitor of AL× series is large, so that AL× series contribute to improve the frequency stability. For the BL× series, the current consumption and drive level reduced so that they can realize the characteristics easier to design small-sized crystal oscillators. The oscillator circuit of each version is simply constructed, so that it can realize the crystal oscillator with excellent phase noise characteristics. Even if the valued characteristics differ due to the application or the purpose, the selecting from these series for different purposes allows the optimization.

FEATURES

■ Operating supply voltage range

• CF5015AL×: 2.25 to 2.75V

CF5015BL×: 2.25 to 5.5V

■ Up to 60MHz oscillation frequency range

■ -40 to 85°C operating temperature range

■ Oscillation capacitors built-in

• CF5015AL×: $C_G = 18pF$, $C_D = 18pF$

• CF5015BL×: $C_G = 4pF$, $C_D = 8pF$

■ Inverter amplifier feedback resistor built-in

■ Standby function

• High impedance in standby mode, oscillator stops

■ Low standby current

• Power-saving pull-up resistor built-in

■ f_O, f_O/2, f_O/4, f_O/8, or f_O/16 output frequency, determined by internal connection

■ CMOS output duty level (1/2VDD)

■ Molybdenum-gate CMOS process

■ Chip form (CF5015×L×)

SERIES CONFIGURATION

	Operating	Recom	mended osc	illation frequ	ency range	¹ [MHz]	Built-in capacitance [pF]			Standby mode	
Version	supply voltage	2.5V op	eration	3∨ ор€	eration	5V operation			capacitance [pF]		Output frequency
	range [V]	C _L = 15pF	C _L = 30pF	C _L = 15pF	C _L = 30pF	C _L = 30pF	C _G	CD		function	state
CF5015AL1					-	-			f_0^{*2}	Yes	
CF5015AL2			4 to 50	-					f _O /2		Hi-Z
CF5015AL3	2.25 to 2.75	4 to 60					18	18	f _O /4		
CF5015AL4									f _O /8		
CF5015AL5									f _O /16		
CF5015BL1									f_0^{*2}		
CF5015BL2	0.05 +- 0.0								f _O /2		
CF5015BL3	2.25 to 3.6 4.5 to 5.5	12 to 60 12 to 50	12 to 50	12 to 60	12 to 50	12 to 60	4	8	f _O /4	Yes	Hi-Z
CF5015BL4									f _O /8		
CF5015BL5										f _O /16	

^{*1.} The recommended oscillation frequency is a yardstick value derived from the crystal used for NPC characteristics authentication. However, the oscillator frequency band is not guaranteed. Specifically, the characteristics can vary greatly due to crystal characteristics and mounting conditions, so the oscillation characteristics of components must be carefully evaluated.

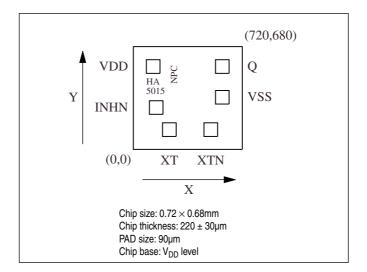
ORDERING INFORMATION

Device	Package
CF5015×L×-2	Chip form

^{*2.} Oscillation frequency

PAD LAYOUT

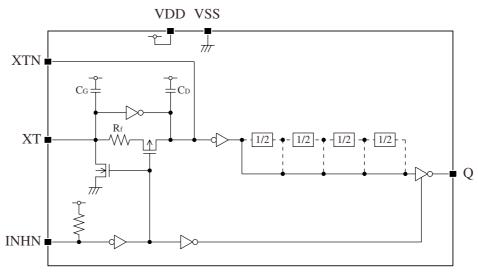
(Unit: µm)



PIN DESCRIPTION and PAD DIMENSIONS

Name	1/0		Pad dimensions [µm]		
Name	1/0		Х	Υ	
INHN	I	Output state control input. High impedance when LOW (oscillator stops). Power-saving pull-up resistor built-in.			277
XT	I	Amplifier input	Crystal connection pins.	238	131
XTN	0	Amplifier output	Crystal is connected between XT and XTN.	512	131
VSS	-	Ground		588	345
Q	0	Output. Output frequency	Output. Output frequency (f _O , f _O /2, f _O /4, f _O /8, f _O /16) determined by internal connection		548
VDD	-	Supply voltage	Supply voltage		

BLOCK DIAGRAM



INHN = LOW active

SPECIFICATIONS

Absolute Maximum Ratings

 $V_{SS} = 0V$

Parameter	Symbol	Condition	Rating	Unit
Supply voltage range	V _{DD}		-0.5 to +7.0	V
Input voltage range	V _{IN}		-0.5 to V _{DD} + 0.5	V
Output voltage range	V _{OUT}		-0.5 to V _{DD} + 0.5	V
Operating temperature range	T _{opr}		-40 to +85	°C
Storage temperature range	T _{STG}		-65 to +150	°C
Output current	I _{OUT}		12	mA

Recommended Operating Conditions

2.5V operation (CF5015AL×/CF5015BL×)

 $V_{SS} = 0V$

Parameter	Symbol	Condition		Rating	Unit
Supply voltage range	V _{DD}			2.25 to 2.75	V
Input voltage range	V _{IN}			V _{SS} to V _{DD}	V
Operating temperature range	T _{OPR}			-40 to +85	°C
Oscillation frequency range		CF5015AL×		4 to 60	MHz
Oscillation nequency range	fo	CF5015BL×		12 to 60	MHz
		CF5015AL×	C _L ≤ 15pF	0.25 to 60	MHz
Output fraguancy range	,	CF5015ALX	C _L ≤ 30pF	0.25 to 50	MHz
Output frequency range	fout	CF5015BL×	C _L ≤ 15pF	0.75 to 60	MHz
		CESUISBLX	C _L ≤ 30pF	0.75 to 50	MHz

3V operation (CF5015BL×)

 $V_{SS} = 0V$

Parameter	Symbol	Condition	Rating	Unit
Supply voltage range	V _{DD}		2.7 to 3.6	V
Input voltage range	V _{IN}		V _{SS} to V _{DD}	V
Operating temperature range	T _{OPR}		-40 to +85	°C
Oscillation frequency range	f _O		12 to 60	MHz
Output fraguency range		C _L ≤ 15pF	0.75 to 60	MHz
Output frequency range	TOUT	$C_L \le 30pF$	0.75 to 50	MHz

5V operation (CF5015BL×)

 $V_{SS} = 0V$

Parameter	Symbol	Condition	Rating	Unit
Supply voltage range	V _{DD}		4.5 to 5.5	V
Input voltage range	V _{IN}		V _{SS} to V _{DD}	V
Operating temperature range	T _{OPR}		-40 to +85	°C
Oscillation frequency range	f _O		12 to 60	MHz
Output frequency range	f _{OUT}	$C_L \le 30pF$	0.75 to 60	MHz

Electrical Characteristics

2.5V operation (CF5015AL×/CF5015BL×)

 $V_{\rm DD}$ = 2.25 to 2.75V, $V_{\rm SS}$ = 0V, Ta = -40 to +85°C unless otherwise noted.

Parameter	Symbol	Condition			Unit		
Parameter	Symbol	Condition		min	typ	max	Unit
HIGH-level output voltage	V _{OH}	Q: Measurement cct 1, V _{DD} = 2.25V, I _{OH} = 4	4mA	1.65	1.95	-	٧
LOW-level output voltage	V _{OL}	Q: Measurement cct 1, V _{DD} = 2.25V, I _{OL} = 4	łmA	_	0.3	0.4	٧
HIGH-level input voltage	V _{IH}	INHN		0.7V _{DD}	-	-	٧
LOW-level input voltage	V _{IL}	INHN		-	-	0.3V _{DD}	٧
		O. Massurament act 0 INILIN I OW	$V_{OH} = V_{DD}$	-	-	10	μA
Output leakage current	IZ	Q: Measurement cct 2, INHN = LOW	V _{OL} = V _{SS}	-	-	10	μA
			CF5015AL1	-	5.5	11	mA
			CF5015AL2	_	4	8	mA
		Measurement cct 3, load cct 1, INHN = open, C _L = 15pF, f = 60MHz	CF5015AL3	-	3	6	mA
			CF5015AL4	-	2.5	5	mA
0	I _{DD}		CF5015AL5	-	2	4	mA
Current consumption			CF5015BL1	-	4.5	9	mA
			CF5015BL2	-	3	6	mA
			CF5015BL3	-	2	4	mA
			CF5015BL4	-	1.5	3	mA
			CF5015BL5	-	1	2	mA
Standby current	I _{ST}	Measurement cct 3, INHN = LOW	•	_	-	3	μA
INI INI mulli un vaniataman	R _{UP1}	Management ant 4		2	6	12	MΩ
INHN pull-up resistance	R _{UP2}	Measurement cct 4		20	100	200	kΩ
Feedback resistance	R _f	Measurement cct 5		100	300	600	kΩ
	_	Design value. A monitor pattern on a	CF5015AL×	15.3	18	20.7	pF
Duilt in consistence	C _G	wafer is tested.	CF5015BL×	3.4	4	4.6	pF
Built-in capacitance		Design value. A monitor pattern on a	CF5015AL×	15.3	18	20.7	pF
	C _D	wafer is tested.	CF5015BL×	6.8	8	9.2	pF

3V operation (CF5015BL×)

 $V_{\rm DD}$ = 2.7 to 3.6V, $V_{\rm SS}$ = 0V, Ta = -40 to +85°C unless otherwise noted.

Damamatan	Combal	ymbol Condition			Rating			
Parameter	Symbol				typ	max	Unit	
HIGH-level output voltage	V _{OH}	Q: Measurement cct 1, V _{DD} = 2.7V, I _{OH} =	Q: Measurement cct 1, V _{DD} = 2.7V, I _{OH} = 4mA		2.4	-	V	
LOW-level output voltage	V _{OL}	Q: Measurement cct 1, V _{DD} = 2.7V, I _{OL} =	4mA	-	0.3	0.4	V	
HIGH-level input voltage	V _{IH}	INHN		0.7V _{DD}	-	_	V	
LOW-level input voltage	V _{IL}	INHN		-	-	0.3V _{DD}	V	
Output leakage current	,	Q: Measurement cct 2, INHN = LOW	$V_{OH} = V_{DD}$	-	-	10	μΑ	
Output leakage current	l _Z		V _{OL} = V _{SS}	-	-	10	μΑ	
		Measurement cct 3, load cct 1, INHN = open, C _L = 15pF, f = 60MHz	CF5015BL1	-	5.5	11	mA	
	I _{DD}		CF5015BL2	-	3	6	mA	
Current consumption			CF5015BL3	-	2	4	mA	
			CF5015BL4	-	1.5	3	mA	
			CF5015BL5	-	1	2	mA	
Standby current	I _{ST}	Measurement cct 3, INHN = LOW	-	-	-	5	μΑ	
INII INI andi na assistance	R _{UP1}	Management and 4		1	4	10	МΩ	
INHN pull-up resistance	R _{UP2}	Measurement cct 4		20	100	200	kΩ	
Feedback resistance	R _f	Measurement cct 5		100	300	600	kΩ	
Duilt in conscitones	C _G	Design value A monitor nottors	or in tootod	3.4	4	4.6	pF	
Built-in capacitance	C _D	Design value. A monitor pattern on a wafer is tested.		6.8	8	9.2	pF	

5V operation (CF5015BL×)

 $V_{\rm DD}$ = 4.5 to 5.5V, $V_{\rm SS}$ = 0V, Ta = -40 to +85°C unless otherwise noted.

Parameter	Combal	Condition		Rating			
Parameter	Symbol	Condition			typ	max	Unit
HIGH-level output voltage	V _{OH}	Q: Measurement cct 1, V _{DD} = 4.5V, I _{OH} = 8mA		3.9	4.2	_	٧
LOW-level output voltage	V _{OL}	Q: Measurement cct 1, V _{DD} = 4.5V, I _{OL} =	8mA	-	0.3	0.4	٧
HIGH-level input voltage	V _{IH}	INHN		0.7V _{DD}	-	-	٧
LOW-level input voltage	V _{IL}	INHN		-	-	0.3V _{DD}	٧
Outrat lealings assument		O. Management and O. INIJIN. J. COM.	$V_{OH} = V_{DD}$	-	-	10	μΑ
Output leakage current	l _Z	Q: Measurement cct 2, INHN = LOW	V _{OL} = V _{SS}	-	-	10	μΑ
		Measurement cct 3, load cct 1, INHN = open, C _L = 30pF, f = 60MHz	CF5015BL1	-	15	30	mA
	I _{DD}		CF5015BL2	-	9.5	19	mA
Current consumption			CF5015BL3	_	6.5	13	mA
			CF5015BL4	-	5	10	mA
			CF5015BL5	-	4	8	mA
Standby current	I _{ST}	Measurement cct 3, INHN = LOW		_	-	10	μA
INII INI mulli um maciatamas	R _{UP1}	Management and 4		0.5	2	8	МΩ
INHN pull-up resistance	R _{UP2}	Measurement cct 4		10	50	150	kΩ
Feedback resistance	R _f	Measurement cct 5		100	300	600	kΩ
Duilt in consistence	C _G	Design value Amerikan nettern en eurof	-	3.4	4	4.6	pF
Built-in capacitance	C _D	Design value. A monitor pattern on a wafer is tested.		6.8	8	9.2	pF

Switching Characteristics

2.5V operation (CF5015AL×/CF5015BL×)

 $V_{\rm DD}$ = 2.25 to 2.75V, $V_{\rm SS}$ = 0V, Ta = -40 to +85°C unless otherwise noted.

Parameter	Symbol	Condition		Rating			- Unit
Parameter	Syllibol	on Condition			typ	max	
Output rise time	t _{r1}	Measurement cct 3, load cct 1,	C _L = 15pF	-	3	6	ns
Output rise tillle	t _{r2}	0.1V _{DD} to 0.9V _{DD}	C _L = 30pF	-	5	10	
Output fall time	t _{f1}	Measurement cct 3, load cct 1,	C _L = 15pF	-	3	6	ns
Output fail time	t _{f2}	0.9V _{DD} to 0.1V _{DD}	C _L = 30pF	-	5	10	
Output duty cycle*1	Duty1	Measurement cct 3, load cct 1,	C _L = 15pF f = 60MHz	45	-	55	%
Output duty cycle	Duty2	V _{DD} = 2.5V, Ta = 25°C	C _L = 30pF f = 50MHz	45	-	55	%
Output disable delay time*2	t _{PLZ}	Measurement cct 6, load cct 1, V _{DD} = 2.5\	/, Ta = 25°C,	-	-	100	ns
Output enable delay time*2	t _{PZL}	C _L = 15pF		_	-	100	ns

^{*1.} The duty cycle characteristic is checked the sample chips of each production lot.

3V operation (CF5015BL×)

 $V_{\rm DD}$ = 2.7 to 3.6V, $V_{\rm SS}$ = 0V, Ta = -40 to +85°C unless otherwise noted.

Parameter	Symbol	mbol Condition			Rating		
raiailletei	Syllibol				typ	max	Unit
Output rise time	t _{r1}	Measurement cct 3, load cct 1,	C _L = 15pF	_	2.5	5	- ns
	t _{r2}	0.1V _{DD} to 0.9V _{DD}	C _L = 30pF	-	4	8	
Output fall time	t _{f1}	Measurement cct 3, load cct 1,	C _L = 15pF	-	2.5	5	ns
Output fall time	t _{f2}	0.9V _{DD} to 0.1V _{DD}	C _L = 30pF	-	4	8	
Output duty cycle*1	Duty1	Measurement cct 3, load cct 1,	C _L = 15pF f = 60MHz	45	-	55	%
Output duty cycle	Duty2	V _{DD} = 3.0V, Ta = 25°C	C _L = 30pF f = 50MHz	45	-	55	%
Output disable delay time*2	t _{PLZ}	Measurement cct 6, load cct 1, V _{DD} = 3.0V, Ta = 25°C,		-	-	100	ns
Output enable delay time*2	t _{PZL}	C _L = 15pF		-	-	100	ns

^{*1.} The duty cycle characteristic is checked the sample chips of each production lot.

^{*2.} Oscillator stop function is built-in. When INHN goes LOW, normal output stops. When INHN goes HIGH, normal output is not resumed until after the oscillator start-up time has elapsed.

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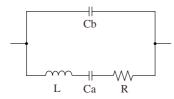
5V operation (CF5015BL×)

 $V_{DD} = 4.5$ to 5.5V, $V_{SS} = 0$ V, Ta = -40 to +85°C unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
Parameter		Condition		min	typ	max	Uill
Output rise time	t _{r1}	Measurement cct 3, load cct 1,	C _L = 15pF	-	1.7	3.4	ns
	t _{r2}	0.1V _{DD} to 0.9V _{DD}	C _L = 30pF	-	3	6	
Output fall time	t _{f1}	Measurement cct 3, load cct 1,	C _L = 15pF	-	1.7	3.4	- ns
	t _{f2}	0.9V _{DD} to 0.1V _{DD}	C _L = 30pF	_	3	6	
Output duty cycle ^{*1}	Duty1	Measurement cct 3, load cct 1, V _{DD} = 5.0V, Ta = 25°C	C _L = 30pF f = 60MHz	45	-	55	%
Output disable delay time*2	t _{PLZ}	Measurement cct 6, load cct 1, V _{DD} = 5.0V, Ta = 25°C,		-	-	100	ns
Output enable delay time*2	t _{PZL}	C _L = 15pF		_	-	100	ns

^{*1.} The duty cycle characteristic is checked the sample chips of each production lot.

Current consumption and Output waveform with NPC's standard crystal



f [MHz]	R [Ω]	L [mH]	Ca [fF]	Cb [pF]
50	16.12	6.88	1.48	1.18
60*	_	_	_	-

^{*} The 60MHz crystal parameter is confidential.

FUNCTIONAL DESCRIPTION

Standby Function

When INHN goes LOW, the oscillator stops and the oscillator output on Q becomes high impedance.

INHN	Q	Oscillator	
HIGH (or open)	HIGH (or open) Any f _O , f _O /2, f _O /4, f _O /8 or f _O /16 output frequency		
LOW High impedance		Stopped	

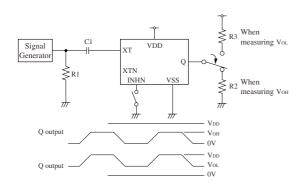
Power-saving Pull-up Resistor

The INHN pull-up resistance changes in response to the input level (HIGH or LOW). When INHN goes LOW (standby state), the pull-up resistance becomes large to reduce the current consumption during standby.

^{*2.} Oscillator stop function is built-in. When INHN goes LOW, normal output stops. When INHN goes HIGH, normal output is not resumed until after the oscillator start-up time has elapsed.

MEASUREMENT CIRCUITS

Measurement cct 1



2Vp-p, 10MHz sine wave input signal

C1: 0.001µF

R1: 50Ω

R2: 413Ω (2.5V operation)

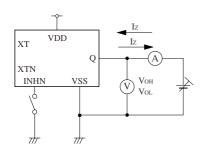
525Ω (3V operation)

488Ω (5V operation)

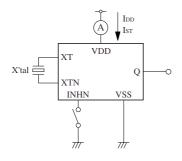
R3: 462Ω (2.5V operation)

 575Ω (3V operation) 512Ω (5V operation)

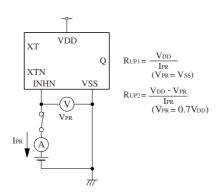
Measurement cct 2



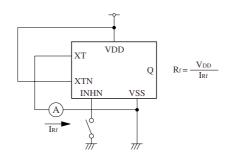
Measurement cct 3



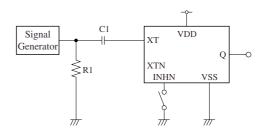
Measurement cct 4



Measurement cct 5



Measurement cct 6

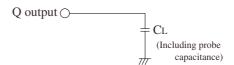


2Vp-p, 10MHz sine wave input signal

C1: 0.001µF

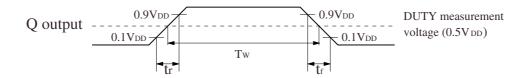
R1: 50Ω

Load cct 1

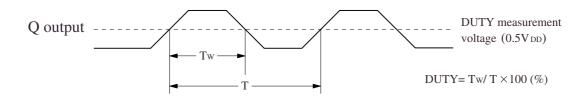


Switching Time Measurement Waveform

Output duty level

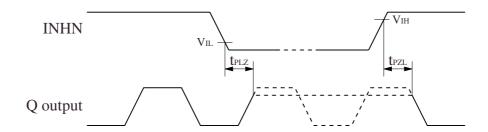


Output duty cycle



Output Enable/Disable Delay

when the device is in standby, the oscillator stops. When standby is released, the oscillator starts and stable oscillator output occurs after a short delay.



INHN input waveform $tr = tf \le 10ns$

Please pay your attention to the following points at time of using the products shown in this document.

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